

2826

**STATEMENT UNDER 37 CFR 1.97(e) ACCOMPANYING
INFORMATION DISCLOSURE STATEMENT**

Docket No.
BUR920000059US1

In Re Application Of: **Bryant et al.**

MAR 31 2003

#7

Serial No.
09/886,823

Filing Date
06/21/01

Examiner
Abraham, F.

Group Art Unit
2826

Invention: **DOUBLE GATED TRANSISTOR AND METHOD OF FABRICATION**

TO THE ASSISTANT COMMISSIONER FOR PATENTS:

This is a statement under the provisions of 37 CFR 1.97(e) in the above-identified application.

Check applicable statement herebelow:

Statement Under 37 CFR 1.97(e)(1)

- Each item of information contained in the accompanying Information Disclosure Statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the Information Disclosure Statement.

Statement Under 37 CFR 1.97(e)(2)

- No item of information contained in the accompanying Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application, and, to the knowledge of the undersigned person, after making reasonable inquiry, no item of information contained in the accompanying Information Disclosure Statement was known to any individual designated in 37 CFR 1.56(c) more than three months prior to the filing of the Information Disclosure Statement.



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Dated: **26 March 2003**

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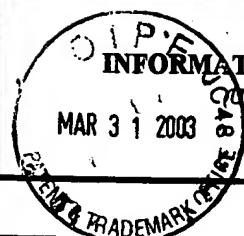
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3/28/03 with the U.S. Postal Service as first class mail under 37 C.F.R. 1.8 and is addressed to the Assistant Commissioner for Patents, Washington, D.C. 20231.



Signature of Person Mailing Correspondence

Pat Blair

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INFORMATION DISCLOSURE CITATION

MAR 31 2003

(Use several sheets if necessary)

Docket Number (Optional)	Application Number
BUR920000059US1	09/886,823
Applicant(s) Bryant et al.	
Filing Date	Group Art Unit
06/21/01	2826

U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO
	EP 0 694 977 A2	01/31/96	European (DE, FR, GB, NL)				

OTHER DOCUMENTS (*Including Author, Title, Date, Pertinent Pages, Etc.*)

Kim K et al., "Double-Gate CMOS: Symmetrical-Versus Asymmetrical-Gate Devices", IEEE Transactions on Electron Devices, IEEE Inc. New York, US, vol. 48, no. 2, February 2001 (2001-02), pages 294-299, XP001038978, ISSN: 0018-9383

EXAMINER _____ **DATE CONSIDERED** _____

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.